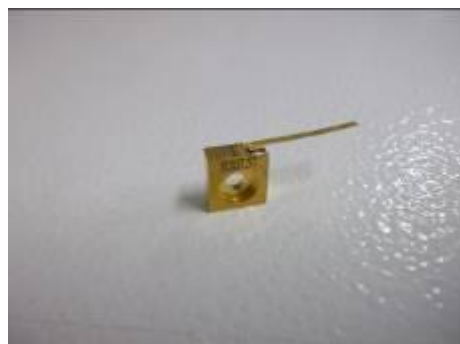


808nm High Power C-mount Laser Diode



Features:

- Output power: 1000/2000/3000/5000mW
- Efficient quantum well structure
- Center Wavelength: 808nm
- Package: C-mount

Absolute Maximum Ratings($T=25\text{ }^{\circ}\text{C}$)

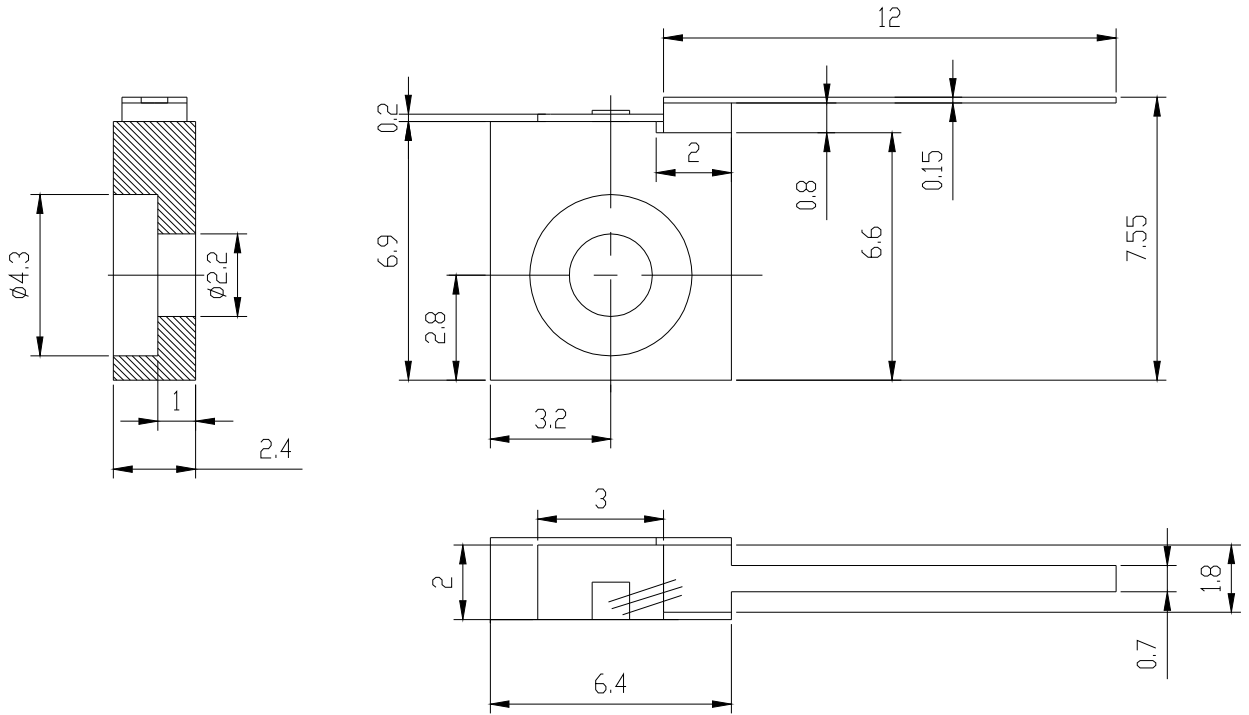
Parameter	Symbol	Unit	Min	Max	Note
Reverse Voltage	V_r	V	-	2	-
Operating Temperature	T_o	$^{\circ}\text{C}$	10	30	
Storage Temperature	T_{stg}	$^{\circ}\text{C}$	10	85	
Solder Temperature	S_{temp}	$^{\circ}\text{C}$	-	260	10 seconds max

Electro-Optical Characteristics($T=25\text{ }^{\circ}\text{C}$)

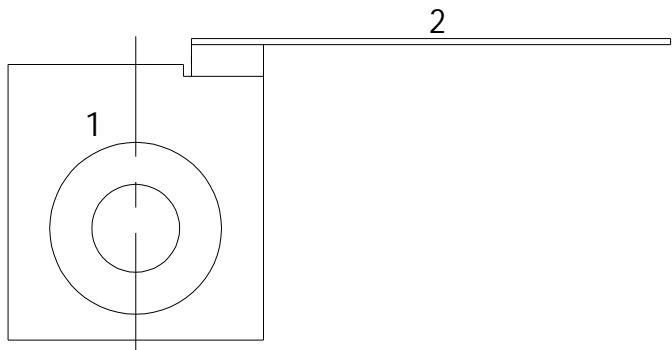
Symbol	Parameter	Unit	AL0808F1000	AL0808F2000	AL0808F3000	AL0808F5000
P_o	Optical output power	mW	1000	2000	3000	5000
λ_c	Center wavelength	nm	808 \pm 5	808 \pm 5	808 \pm 5	808 \pm 5
$\Delta\lambda$	Spectral width	nm	\leq 3.5	\leq 5	\leq 5	\leq 5
I_{th}	Threshold current	mA	\leq 300	\leq 500	\leq 600	\leq 1000
I_o	Operating current	mA	\leq 1300	\leq 2500	\leq 3700	\leq 6000
V_f	Operating voltage	V	1.7~2.0	1.8~2.2	1.8~2.2	1.8~2.4
η	Slope Efficiency	W/A	\geq 1	\geq 1	\geq 1	\geq 1
$\theta_{//} \times \theta_{\perp}$	Beam divergence	o/o	12/40	12/40	12/40	12/40
$\theta_{//} \times \theta_{\perp}$	Beam divergence (fast axis collimated)	o/o	12/10	12/10	12/10	12/10
$d\lambda/dT$	Wavelength temperature coefficient	nm/ $^{\circ}\text{C}$	\leq 0.3	\leq 0.3	\leq 0.3	\leq 0.3

	Emitting area	μm	80×1	100×1	100×1	200×1
	Polarization Ratio		TE	TM	TE	TE

Outline Drawings (in: mm)



Pin Assignment:



Type \ Pin	1	2
09	LD Anode	LD Cathode